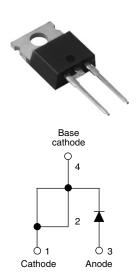


#### Vishay High Power Products

# HEXFRED® Ultrafast Soft Recovery Diode, 4 A



**TO-220AC** 

PRODUCT SUMMARY				
V <sub>R</sub>	600 V			
V <sub>F</sub> at 4 A at 25 °C	1.8 V			
I <sub>F(AV)</sub>	4 A			
t <sub>rr</sub> (typical)	17 ns			
T <sub>J</sub> (maximum)	150 °C			
Q <sub>rr</sub>	40 nC			
dI <sub>(rec)M</sub> /dt	280 A/μs			

#### **FEATURES**

- · Ultrafast recovery
- · Ultrasoft recovery
- Very low I<sub>RRM</sub>
- Very low Q<sub>rr</sub>
- · Specified at operating temperature
- · Lead (Pb)-free
- · Designed and qualified for industrial level

#### **BENEFITS**

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

HFA04TB60 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A continuous current, the HFA04TB60 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the t<sub>b</sub> portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA04TB60 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V <sub>R</sub>		600	V	
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	4		
Single pulse forward current	I <sub>FSM</sub>		25	Α	
Maximum repetitive forward current	I <sub>FRM</sub>		16		
Maximum namer dissination	P <sub>D</sub>	T <sub>C</sub> = 25 °C	25	W	
Maximum power dissipation		T <sub>C</sub> = 100 °C	10		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to + 150	°C	

<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply

### HFA04TB60PbF

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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V <sub>BR</sub>	Ι <sub>R</sub> = 100 μΑ		600	-	-	
		I <sub>F</sub> = 4.0 A		-	1.5	1.8	V
Maximum forward voltage	$V_{FM}$	I <sub>F</sub> = 8.0 A	See fig. 1	-	1.8	2.2	
		I <sub>F</sub> = 4.0 A, T <sub>J</sub> = 125 °C		-	1.4	1.7	
Maximum reverse	,	$V_R = V_R$ rated	See fig. 2	-	0.17	3.0	
leakage current	I <sub>RM</sub>	$T_J = 125 ^{\circ}\text{C},  V_R = 0.8  \text{x}  V_R  \text{rated}$	See lig. 2	-	44	300	μΑ
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	See fig. 3	ı	4.0	8.0	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body		-	8.0	-	nH

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	17	-	
Reverse recovery time See fig. 5, 6 and 16	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	28	42	ns
occ fig. o, o and fo	t <sub>rr2</sub> T <sub>J</sub> = 125 °C	-	38	57			
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 4 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	2.9	5.2	А
See fig. 7 and 8	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	3.7	6.7	
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	40	60	nC
See fig. 9 and 10	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	70	105	110
Peak rate of fall of recovery current during t <sub>b</sub>	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	280	-	A/µs
See fig. 11 and 12	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	235	-	Ανμδ

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	5.0	
Thermal resistance, junction to ambient	R <sub>thA</sub>	Typical socket mount	-	-	80	K/W
Thermal resistance, case to heatsink	R <sub>thS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-	
Weight			-	2.0	-	g
vveigni			-	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-220AC	HFA04TB60			



## HEXFRED® Vishay High Power Products Ultrafast Soft Recovery Diode, 4 A

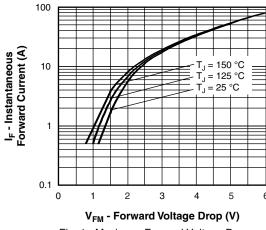


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

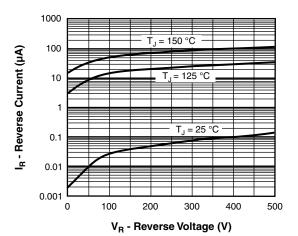


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

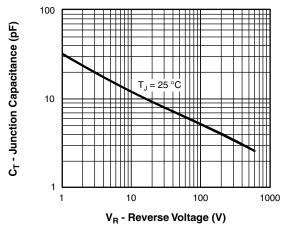


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

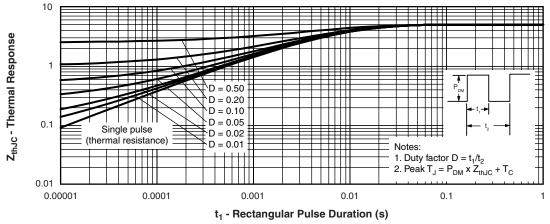


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

#### HFA04TB60PbF

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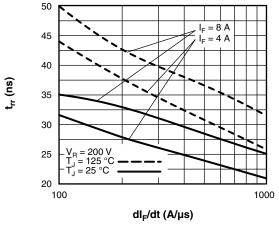


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

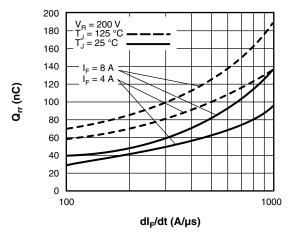


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

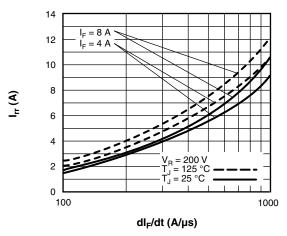


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

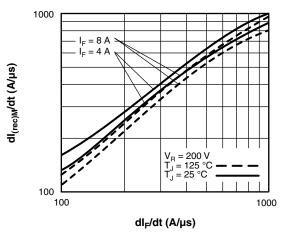


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$ 



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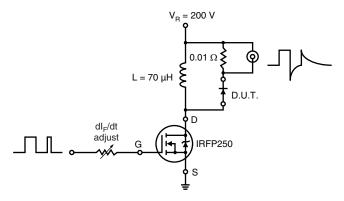
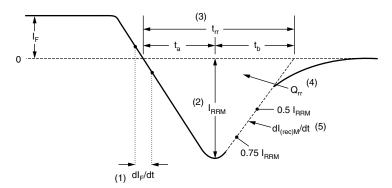


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $\rm I_{RRM}$  peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 10 - Reverse Recovery Waveform and Definitions

LINKS TO RELATED DOCUMENTS				
Dimensions http://www.vishay.com/doc?95221				
Part marking information	http://www.vishay.com/doc?95224			



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Revision: 18-Jul-08

Document Number: 91000 www.vishay.com